

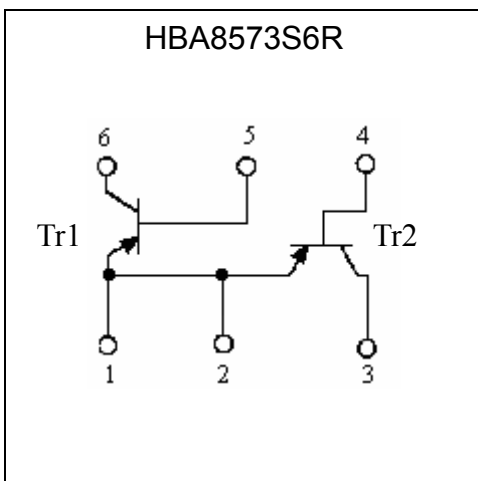
**General Purpose PNP Epitaxial Planar Transistors
 (dual transistors)**

HBA8573S6R

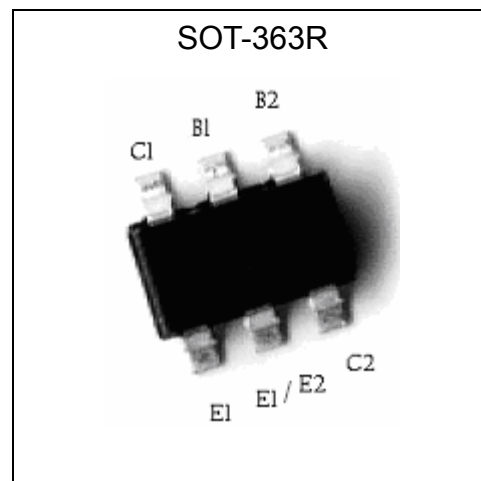
Features

- Two BTA1037 chips in a SOT-363R package.
- Mounting possible with SOT-323 automatic mounting machines.
- Transistor elements are independent, eliminating interference.
- Mounting cost and area can be cut in half.
- Excellent hFE linearity.
- Pb-free package.

Equivalent Circuit



Outline



The following characteristics apply to both Tr1 and Tr2

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CB0}	-60	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EB0}	-6	V
Collector Current	I _C	-150	mA
Power Dissipation	P _D	200(total) *1	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~+150	°C

Note : *1 150mW per element must not be exceeded



Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-60	-	-	V	IC=-50μA
BVCEO	-50	-	-	V	IC=-1mA
BVEBO	-6	-	-	V	IE=-50μA
ICBO	-	-	-0.1	μA	VCB=-60V
IEBO	-	-	-0.1	μA	VEB=-6V
*VCE(sat)	-	-0.2	-0.5	V	IC=-50mA, IB=-5mA
*hFE	120	-	820		VCE=-6V, IC=-1mA
fT	80	180	-	MHz	VCE=-10V, IC=-1mA, f=100MHz
Cob	-	2	3.5	pF	VCB=-10V, f=1MHz

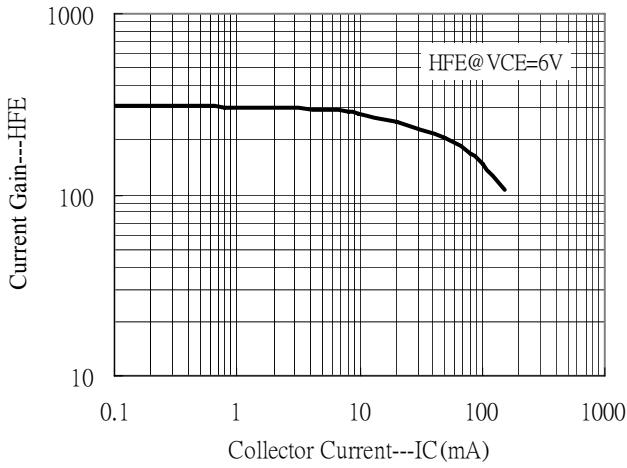
*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

Ordering Information

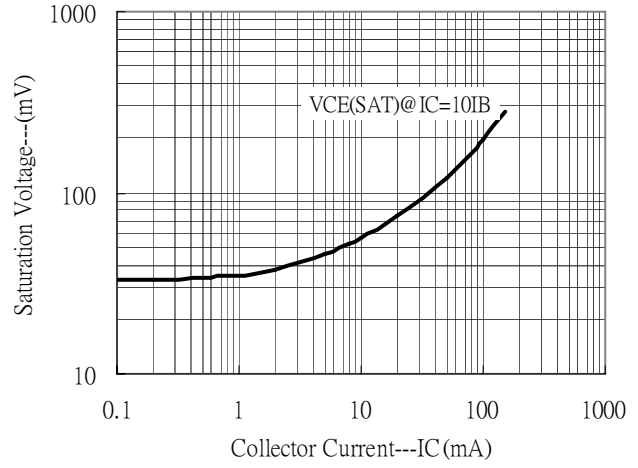
Device	Package	Shipping	Marking
HBA8573S6R	SOT-363 (Pb-free)	3000 pcs / Tape & Reel	BL

Characteristic Curves

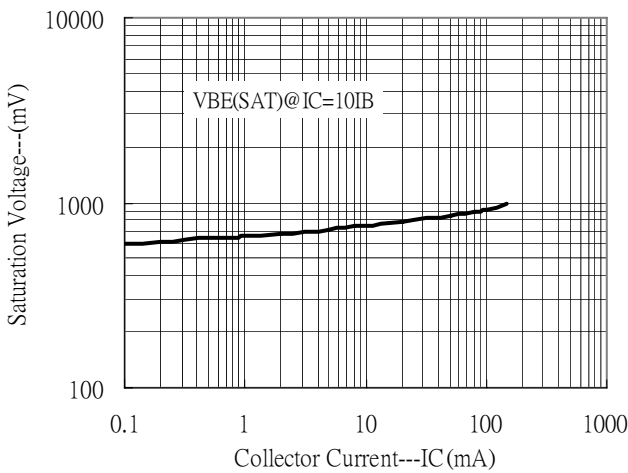
Current Gain vs Collector Current



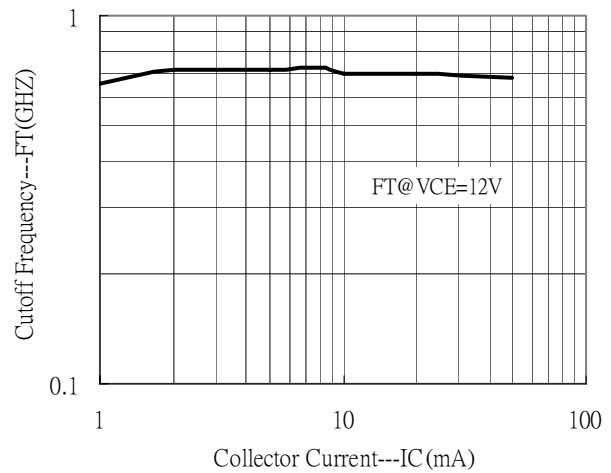
Saturation Voltage vs Collector Current



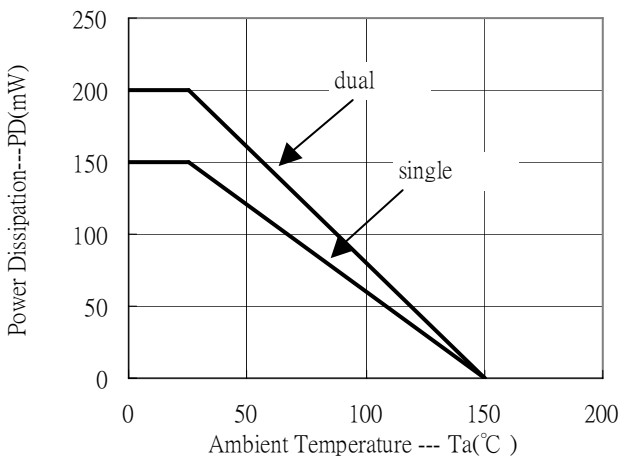
Saturation Voltage vs Collector Current



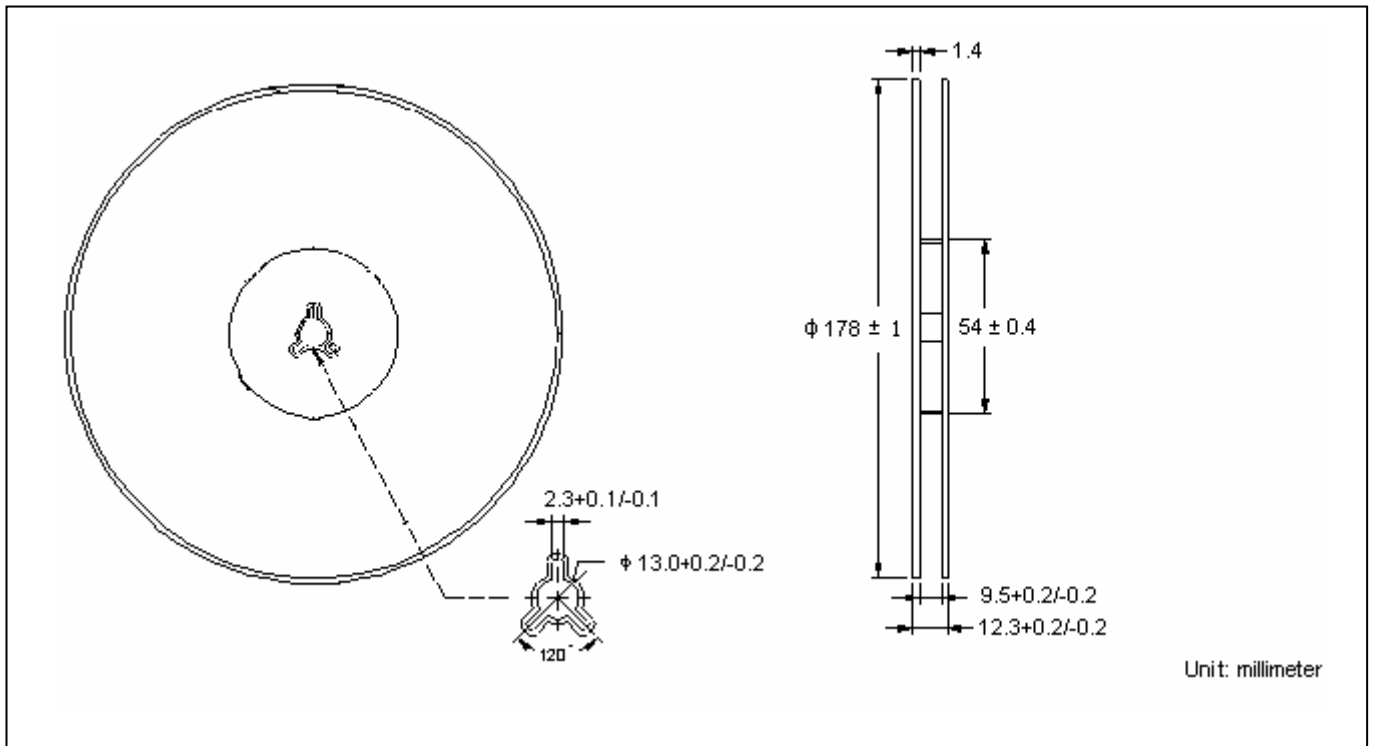
Cutoff Frequency vs Collector Current



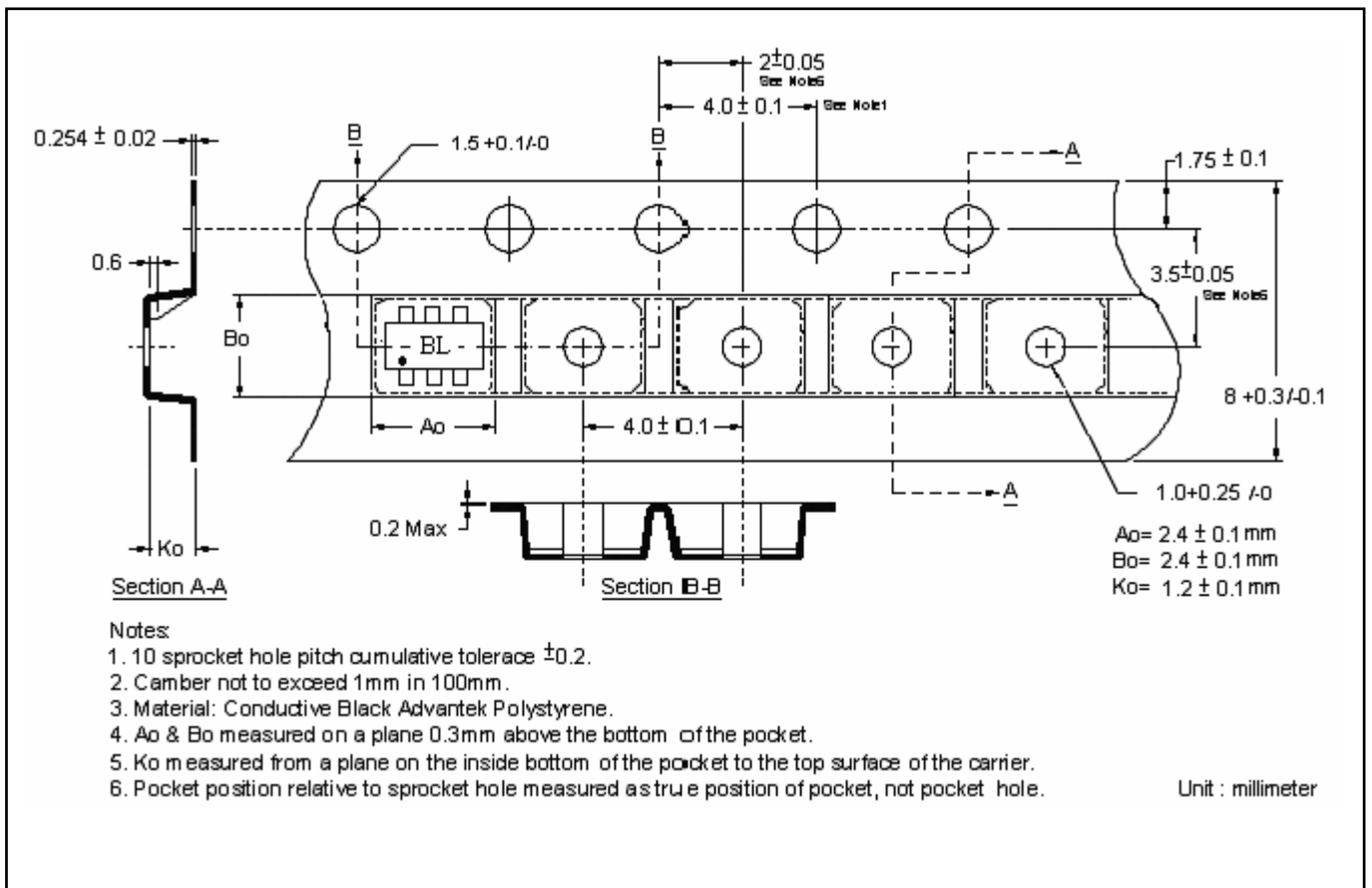
Power Derating Curves



Reel Dimension



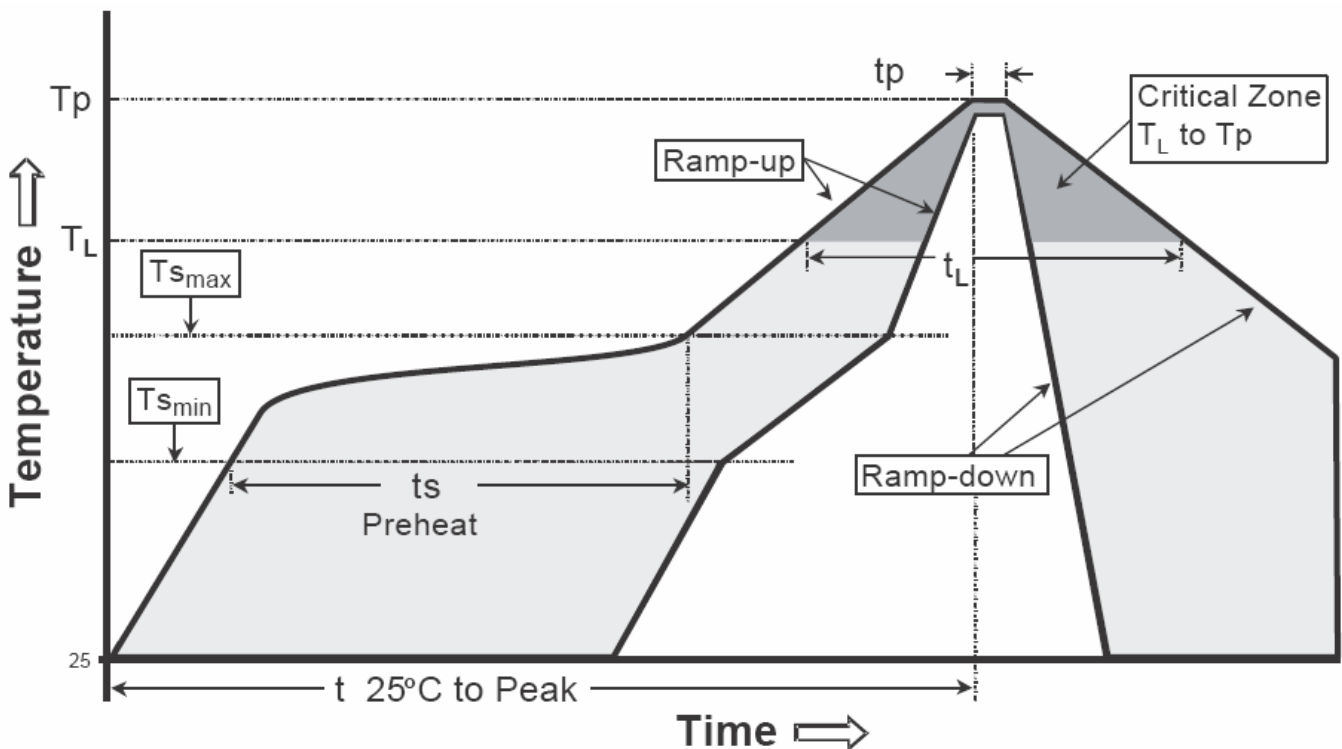
Carrier Tape Dimension



Recommended wave soldering condition

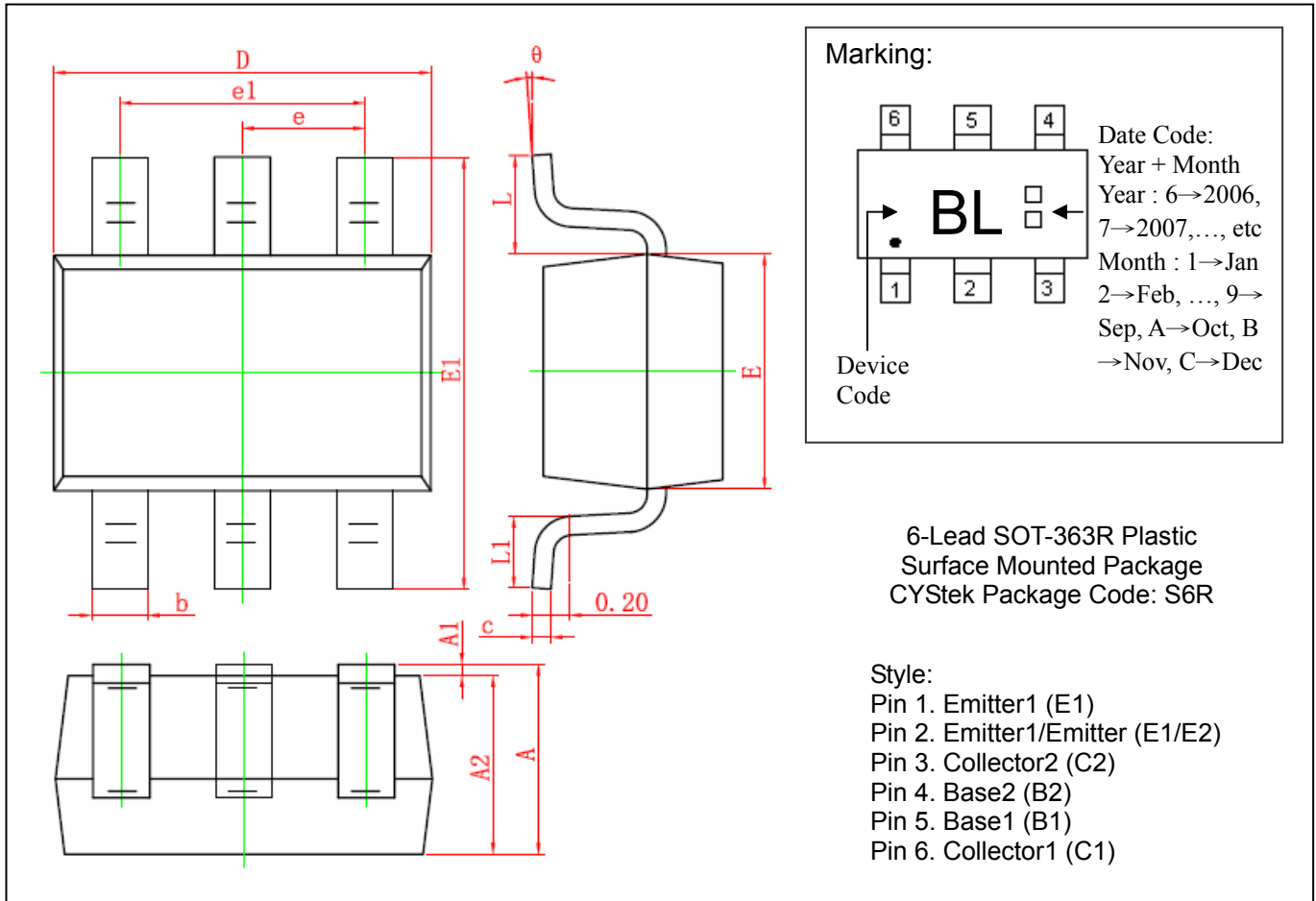
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

SOT-363 Dimension



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043	E1	2.150	2.450	0.085	0.096
A1	0.000	0.100	0.000	0.004	e	0.650	TYP	0.026	TYP
A2	0.900	1.000	0.035	0.039	e1	1.200	1.400	0.047	0.055
b	0.150	0.350	0.006	0.014	L	0.525	REF	0.021	REF
c	0.080	0.150	0.003	0.006	L1	0.260	0.460	0.010	0.018
D	2.000	2.200	0.079	0.087	θ	0°	8°	0°	8°
E	1.150	1.350	0.045	0.053					

Notes : 1. Controlling dimension : millimeters.
 2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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